TELEFUNKEN

Regelbare HF- und ZF-Pentode mit Diode

Remote cutoff RF/IF-pentode with diode

U_f	**6,3**	V
I_f	**300**	mA

Normierte Anheizzeit · Normalized heater warm-up time

Meßwerte · Measuring values

Pentode

U_a	**250**	**250**	V
U_{g3}	**0**	**0**	V
U_{g2}	**80**	**100**	V
U_{g1}	−1	−2	V
I_a	**9**	**9**	mA
I_{g2}	2,7	2,7	mA
S	4,5	3,8	mA/V
R_i	0,9	1	MΩ
$\mu_{g2/g1}$	20	20	

Diode

U_d	10	V
I_d	≧ 0,7	mA

Betriebswerte · Typical operation

Pentode

HF/ZF-Verstärker · RF/IF-amplifier

$U_a = U_b$	**200**		**250**		V
U_{g3}	**0**		**0**		V
R_{g2}	**43**		**62**		kΩ
R_k	**82**		**82**		Ω
U_{bg1}	0	−20	0	−20	V
I_a	**9**	—	**9**	—	mA
I_{g2}	2,8	—	2,7	—	mA
S [1]	4,5	0,12	4,5	0,2	mA/V
R_i [1]	0,65	—	0,9	—	MΩ

[1] Ist R_k nicht kapazitiv überbrückt, wird S ca. 30% kleiner und R_i ca. 10% größer
If R_k is not capacitively shunted, then S is approx. 30% lower and R_i is approx. 10% higher

Grenzwerte · Maximum ratings

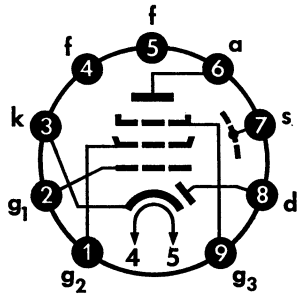
Pentode		
U_{ao}	**550**	V
U_a	**300**	V
N_a	**2,25**	W
U_{g2o}	**550**	V
U_{g2}	**300**	V
N_{g2}	**0,45**	W
I_k	**16,5**	mA
R_{g1} [1]	**3**	MΩ
R_{g3}	**10**	kΩ
$U_{f/k}$	**±100**	V
$R_{f/k}$	**20**	kΩ
Diode		
$-U_{dsp}$	**200**	V
I_d	**0,8**	mA
I_{dsp}	**5**	mA

Kapazitäten · Capacitances

c_e		5	pF
c_a		5,2	pF
$c_{g1/a}$	<	0,0025	pF
$c_{g/f}$	<	0,060	pF
$c_{d/k}$		2,5	pF
$c_{d/f}$	<	0,003	pF
$c_{a/d}$	<	0,025	pF
$c_{g1/d}$	<	0,001	pF

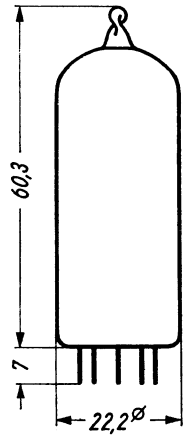
[1]) Auch für $U_{g1\,fest}$ · Also for fixed grid bias

Sockelschaltbild
Basing diagram



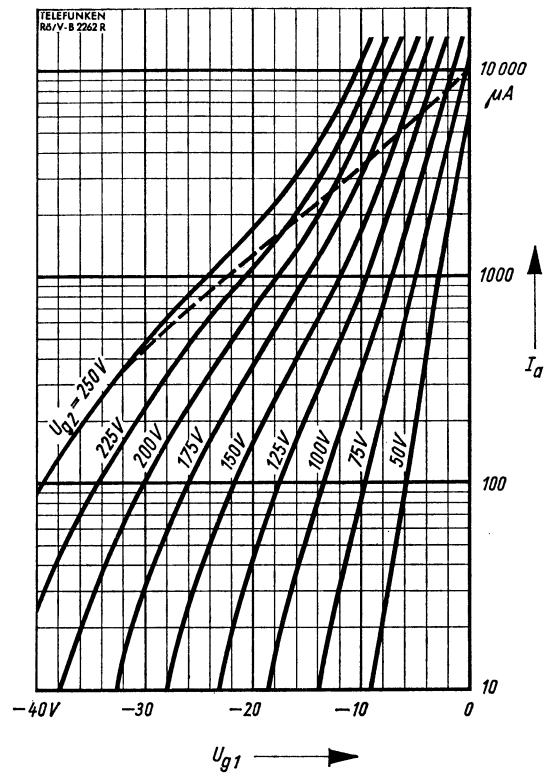
Pico 9 · Noval

max. Abmessungen
max. dimensions
DIN 41 539, Nenngröße 50, Form A



Gewicht · Weight
max. 18 g

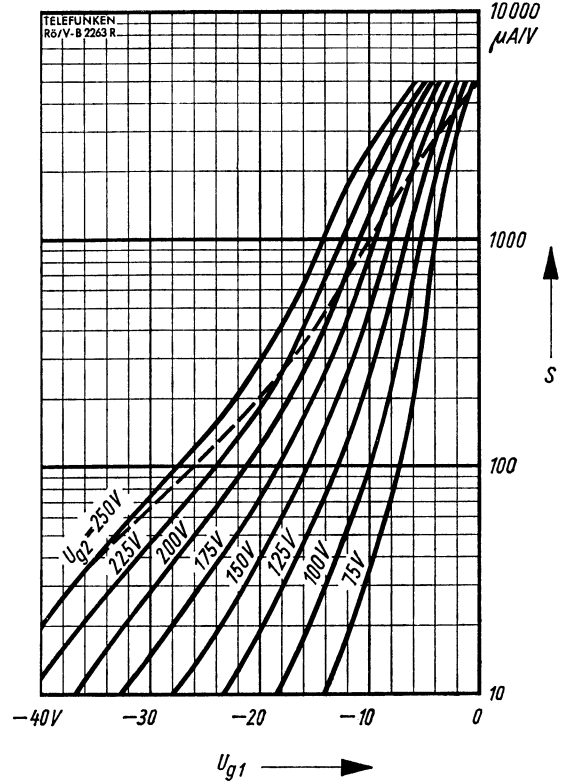
Wenn notwendig, muß gegen Herausfallen der Röhre aus der Fassung Vorsorge getroffen werden.
Special precautions must be taken to prevent the tube from becoming dislodged.



$I_a = f(U_{g1})$

——— U_a = 250 V
U_{g3} = 0 V
U_{g2} = Parameter

---- U_a = 250 V
U_{g3} = 0 V
U_{bg2} = 250 V
R_{g2} = 62 kΩ



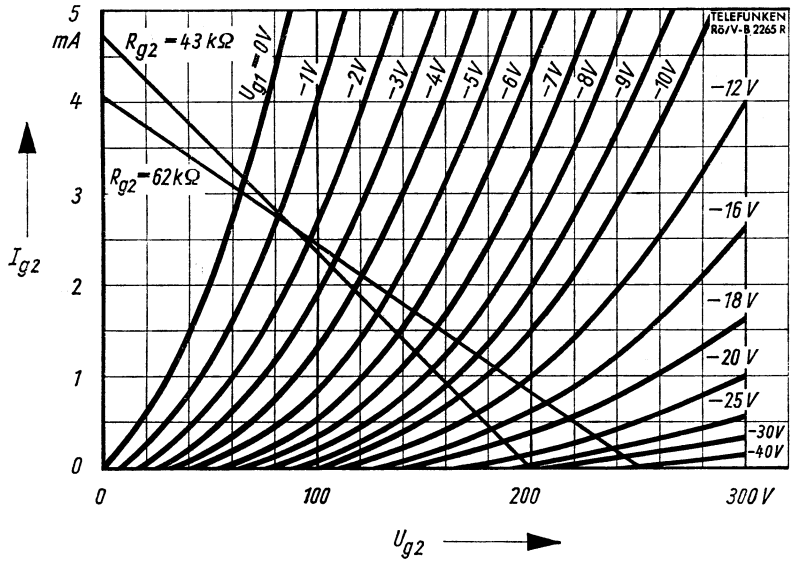
$S = f(U_{g1})$

——— U_a = 250 V
U_{g3} = 0 V
U_{g2} = Parameter

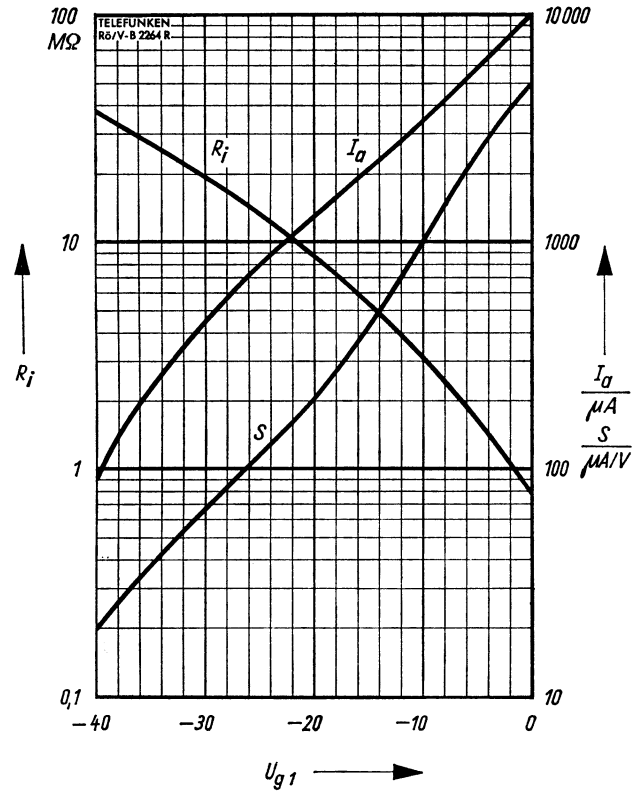
---- U_a = 250 V
U_{g3} = 0 V
U_{bg2} = 250 V
R_{g2} = 62 kΩ

TELEFUNKEN

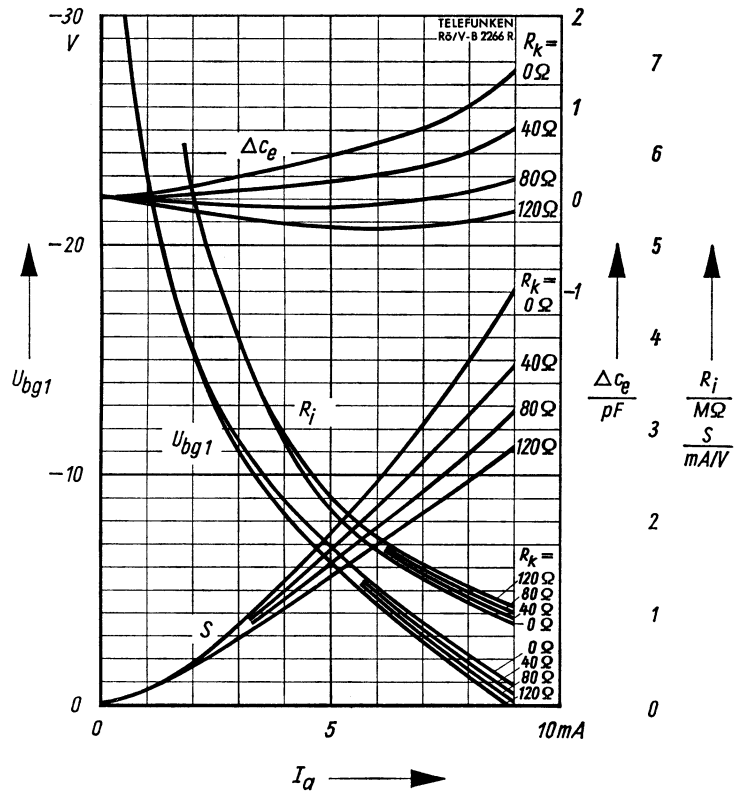
EAF 801



I_{g2} = f (U_{g2})
U_a = 250 V
U_{g3} = 0 V
U_{g1} = Parameter



$I_a, S, R_i = f(U_{g1})$
$U_a = U_{bg2} = 250\ V$
$U_{g3} = 0\ V$
$R_{g2} = 62\ k\Omega$



$U_{bg1}, S, R_i, \Delta c_e = f(I_a)$
$U_b = 250\ V$
$U_{g3} = 0\ V$
$R_{g2} = 62\ k\Omega$
R_k = Parameter

R_k nicht kapazitiv überbrückt · R_k not capacitively shunted